

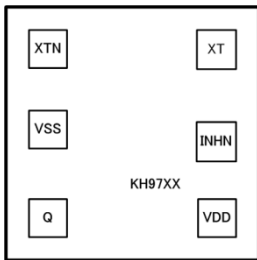
Overview

The high temperature version is built up by strict final test based on stable process capability. An oscillation amplifier is featured with a damping resistor to reduce crystal drive current and suppress frequency deviation with VDD varying. ESD and latch-up test have complied with AEC-Q100 standard.

Features

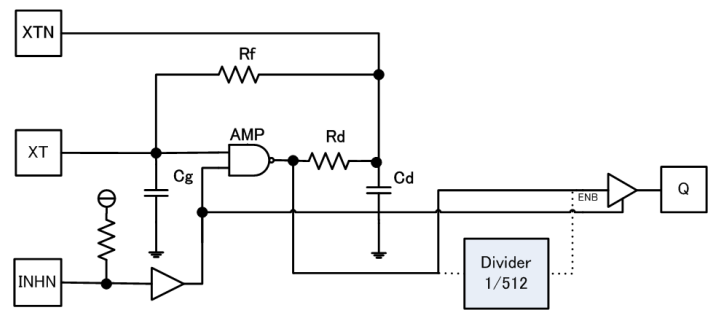
Oscillation frequency (Fundamental)	16.777216MHz
Output frequency 16.777216MHz/512	32.768KHz
Operating Voltage	2.25 ~ 5.5V
Operating Temperature	-40 ~ 85°C
Standby Mode INHN="L"	Q Output "Hi-z" Oscillation Stopped
INHN Input Voltage Level	C-MOS
Q Output Duty Level	C-MOS
Q Output Current	2.6mA (VDD=2.7V)
Q Output Load (Drive Capacity)	50pF

PAD Locations



Chip Size	0.80×0.80mm
PAD Size	90×90um
Chip Thickness	200±20um
Chip Base	VSS Level

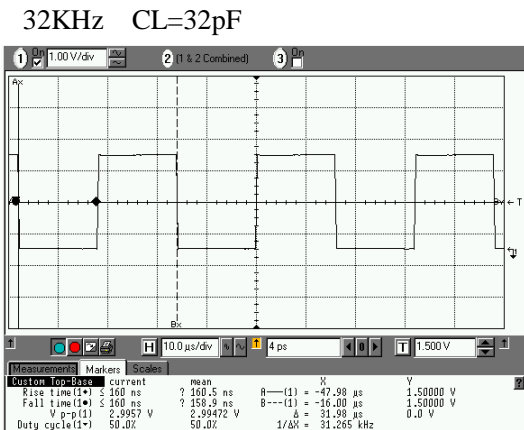
Block Diagram



Reliability

Test Model		Performance Values
ESD	HBM	>4000V
	MM	>400V
	FI-CDM	>1000V
Latch-up	Current Test	>200mA
	Voltage Test	>8.3V

Output waveform



Notes: The document is a brief data sheet of the product.

Please contact with us by email for detailed data sheet, when needed.